

CLEAN COPY OF THE CLAIMS AS AMENDED

Sub D1
B1
1 (Amended). An anisotropic etch mixture for a silicon substrate connected to a low power bias source consisting of one or more of a fluorine-containing gas selected from the group consisting of SF_6 , Si_2F_6 and SiF_4 , HBr and oxygen.

4 (Amended). An etch mixture for silicon consisting essentially of a fluorine-containing gas that includes SF_6 , Si_2F_6 and SiF_4 and HBr and oxygen.